NSN 5961-01-413-3879

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-413-3879 **Inclosure Material:** Metal **Overall Length:** 1.645 inches Overall Diameter: 0.505 inches **Mounting Facility Quantity: Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.559 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 repetitive peak off-state voltage and 30.0 peak gate voltage **Current Rating Per Characteristic:** 40.00 amperes forward current, total rms horsepower metric and 300.00 amperes peak forward surge current absolute **Power Rating Per Characteristic:** 40.0 watts small-signal input power, common-collector blank and 0.75 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 110.0 degrees celsius junction **Test Data Document:** 05869-723097-23 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No